

Silicon NPN Power Transistors

BU426AF

DESCRIPTION

- With TO-3PML package
- High voltage ,high speed

APPLICATIONS

- Intended for use in switching-mode color TV supply systems

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

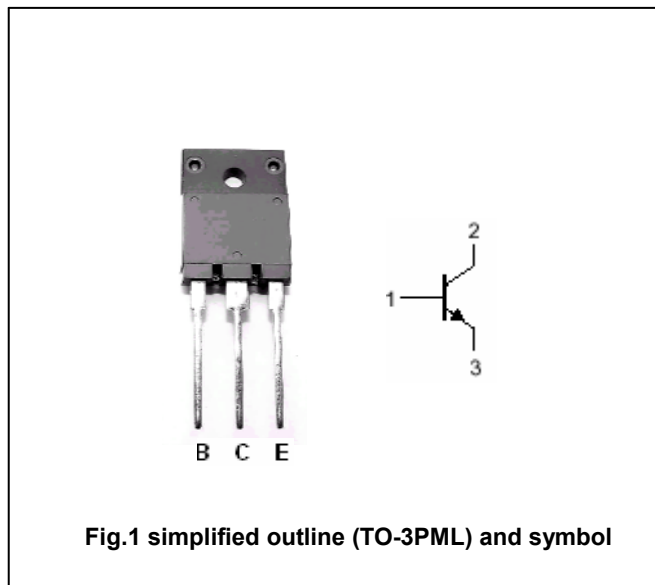


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	900	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	10	V
I <sub>C</sub>	Collector current (DC)		6	A
I <sub>CM</sub>	Collector current (Pulse)		8	A
I <sub>B</sub>	Base current		3	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	65	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	2.08	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA; I <sub>B</sub> =0	400			V
V <sub>CEsat-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.5A			1.5	V
V <sub>CEsat-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =1.25A			3.0	V
V <sub>BEsat-1</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.5A			1.4	V
V <sub>BEsat-2</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A; I <sub>B</sub> =1.25A			1.6	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =900V; V <sub>BE</sub> =0 T <sub>C</sub> =125°C			1.0 2.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =10V; I <sub>C</sub> =0			10	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.6A; V <sub>CE</sub> =5V		30	60	

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =2.5A; V <sub>CC</sub> =250V I <sub>B1</sub> =0.5A			0.5	μs
t <sub>stg</sub>	Storage time	I <sub>C</sub> =2.5A; V <sub>CC</sub> =250V I <sub>B1</sub> =0.5A; I <sub>B2</sub> =-1A			3.5	μs
t <sub>f</sub>	Fall time				0.5	μs

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PACKAGE OUTLINE

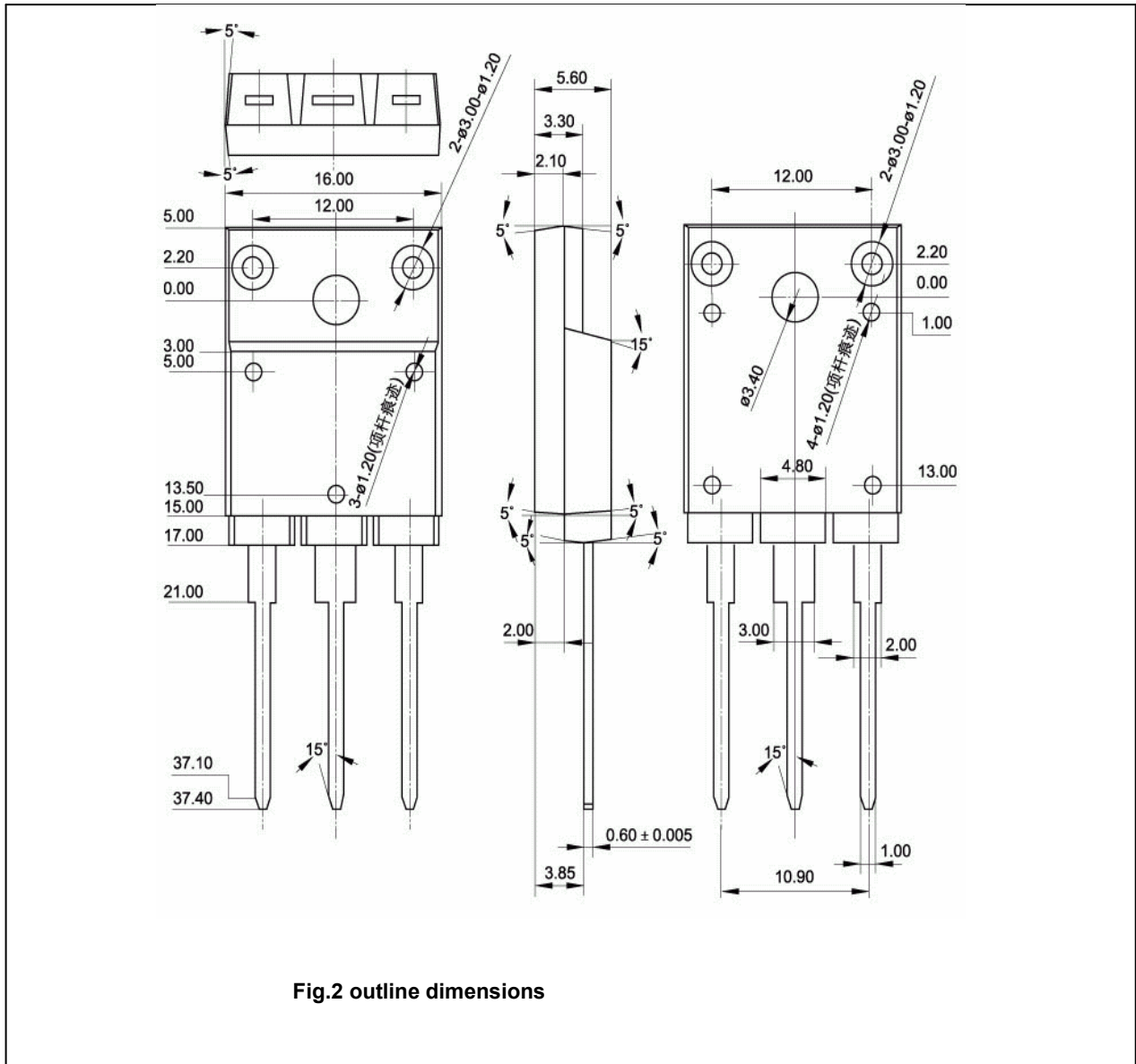


Fig.2 outline dimensions